

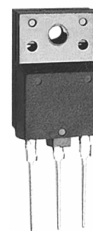


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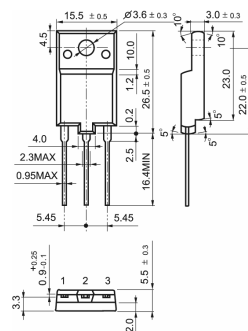
Silicon Diffused Power Transistor

GENERAL DESCRIPTION

Highvoltage,high-speed switching npn transistors in a plastic package,primarily for use in switching power circuites of colour television receivers



TO-3PM



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0V$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	600	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value		-	10	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25^\circ C$	-	50	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 4.0A; I_B = 1.2A$	-	5	V
I_{csat}	Collector saturation current	$f = 16KHz$	-	-	A
V_F	Diode forward voltage	$I_F = 4.0A$	1.5	2.0	V
t_f	Fall time	$I_{Csat} = 4.0A; f = 16KHz$	0.3	1.0	μs

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0V$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	600	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value		-	10	A
I_B	Base current (DC)		-	2	A
I_{BM}	Base current peak value		-	-	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25^\circ C$	-	50	W
T_{sto}	Storage temperature		-55	150	$^\circ C$
T_j	Junction temperature		-	150	$^\circ C$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
I_{CE}	Collector cut-off current	$V_{BE} = 0V; V_{CE} = V_{CESMmax}$	-	1.0	mA
I_{CES}		$V_{BE} = 0V; V_{CE} = V_{CESMmax}$	-	2.5	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	$T_j = 125^\circ C$ $I_B = 0A; I_C = 100mA$ $L = 25mH$	-	-	V
V_{CEsat}	Collector-emitter saturation voltages	$I_C = 4.0A; I_B = 1.2A$	-	5	V
V_{BESat}	Base-emitter saturation voltage	$I_C = 4.0A; I_B = 1.2A$	-	1.5	V
h_{FE}	DC current gain	$I_C = 1A; V_{CE} = 5V$	8	40	
V_F	Diode forward voltage	$I_F = 4.0A$	1.5	2.0	V
f_T	Transition frequency at $f = 5MHz$	$I_C = 0.1A; V_{CE} = 10V$	3	-	MHz
C_c	Collector capacitance at $f = 1MHz$	$V_{CB} = 10V$	230	-	pF
t_s	Switching times(16KHz line deflecton circuit)	$I_C=4A, I_{B(end)}=1.2A, V_{CC}=100V$	-	-	μs
t_f	Turn-off storage time Turn-off fall time	$I_C=4A, I_{B(end)}=1.2A, V_{CC}=100V$	0.3	1.0	μs